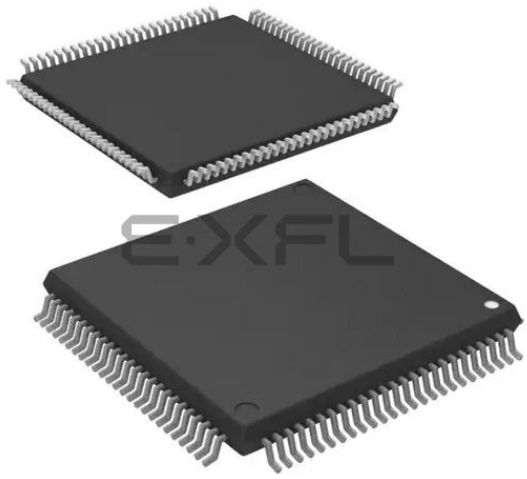
Renesas Electronics America Inc - M30626FHPGP#U3C Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	31K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30626fhpgp-u3c

Table 1.8 Product Code of Flash Memory version and ROMless version for M16C/62P

	Product Code	Package	Internal ROM (User ROM Area Without Block A, Block 1)		Internal ROM (Block A, Block 1)		Operating Ambient Temperature
			Program and Erase Endurance	Temperature Range	Program and Erase Endurance	Temperature Range	
Flash memory Version	D3	Lead-included	100	0°C to 60°C	100	0°C to 60°C	-40°C to 85°C
	D5						-20°C to 85°C
	D7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	D9					-20°C to 85°C	-20°C to 85°C
	U3	Lead-free	100		100	0°C to 60°C	-40°C to 85°C
	U5						-20°C to 85°C
	U7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	U9					-20°C to 85°C	-20°C to 85°C
ROM-less version	D3	Lead-included	–	–	–	–	-40°C to 85°C
	D5						-20°C to 85°C
	U3	Lead-free	–	–	–	–	-40°C to 85°C
	U5						-20°C to 85°C

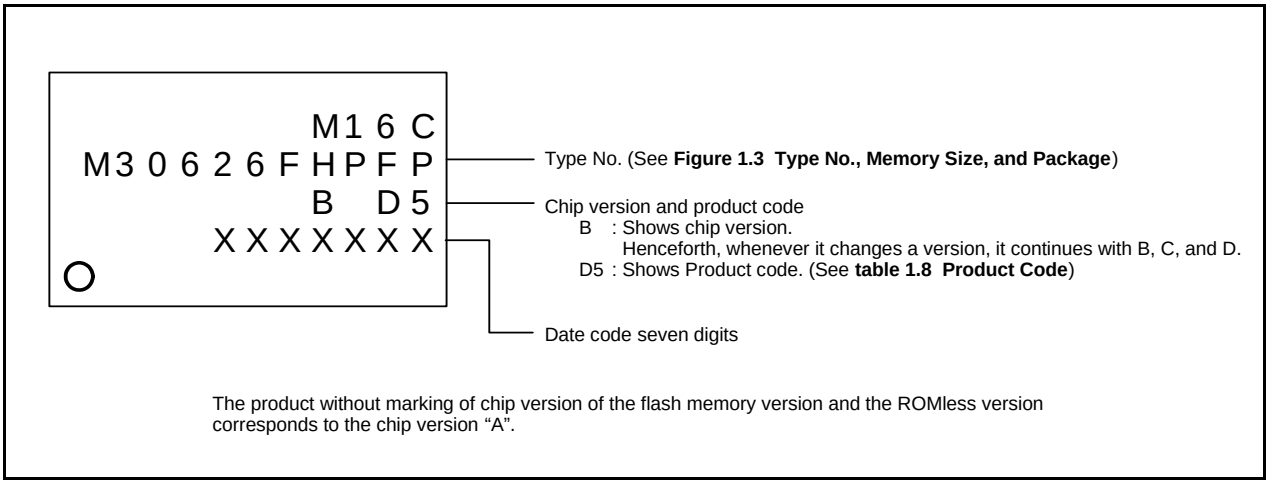

Figure 1.4 Marking Diagram of Flash Memory version and ROM-less version for M16C/62P (Top View)

Table 1.18 Pin Description (100-pin and 128-pin Version) (2)

Signal Name	Pin Name	I/O Type	Power Supply(1)	Description
Main clock input	XIN	I	VCC1	I/O pins for the main clock generation circuit. Connect a ceramic resonator or crystal oscillator between XIN and XOUT (3). To use the external clock, input the clock from XIN and leave XOUT open.
Main clock output	XOUT	O	VCC1	
Sub clock input	XCIN	I	VCC1	I/O pins for a sub clock oscillation circuit. Connect a crystal oscillator between XCIN and XCOUT (3). To use the external clock, input the clock from XCIN and leave XCOUT open.
Sub clock output	XCOUT	O	VCC1	
BCLK output (2)	BCLK	O	VCC2	Outputs the BCLK signal.
Clock output	CLKOUT	O	VCC2	The clock of the same cycle as fC, f8, or f32 is outputted.
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT2}}$	I	VCC1	Input pins for the $\overline{\text{INT}}$ interrupt.
	$\overline{\text{NT3}}$ to $\overline{\text{INT5}}$	I	VCC2	
$\overline{\text{NMI}}$ interrupt input	$\overline{\text{NMI}}$	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt. Pin states can be read by the P8_5 bit in the P8 register.
Key input interrupt input	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	VCC1	Input pins for the key input interrupt.
Timer A	TA0OUT to TA4OUT	I/O	VCC1	These are timer A0 to timer A4 I/O pins. (however, output of TA0OUT for the N-channel open drain output.)
	TA0IN to TA4IN	I	VCC1	These are timer A0 to timer A4 input pins.
	ZP	I	VCC1	Input pin for the Z-phase.
Timer B	TB0IN to TB5IN	I	VCC1	These are timer B0 to timer B5 input pins.
Three-phase motor control output	U, $\overline{\text{U}}$, V, $\overline{\text{V}}$, W, $\overline{\text{W}}$	O	VCC1	These are Three-phase motor control output pins.
Serial interface	$\overline{\text{CTS0}}$ to $\overline{\text{CTS2}}$	I	VCC1	These are send control input pins.
	$\overline{\text{RTS0}}$ to $\overline{\text{RTS2}}$	O	VCC1	These are receive control output pins.
	CLK0 to CLK4	I/O	VCC1	These are transfer clock I/O pins.
	RXD0 to RXD2	I	VCC1	These are serial data input pins.
	SIN3, SIN4	I	VCC1	These are serial data input pins.
	TXD0 to TXD2	O	VCC1	These are serial data output pins. (however, output of TXD2 for the N-channel open drain output.)
	SOUT3, SOUT4	O	VCC1	These are serial data output pins.
	CLKS1	O	VCC1	This is output pin for transfer clock output from multiple pins function.
I^2C mode	SDA0 to SDA2	I/O	VCC1	These are serial data I/O pins. (however, output of SDA2 for the N-channel open drain output.)
	SCL0 to SCL2	I/O	VCC1	These are transfer clock I/O pins. (however, output of SCL2 for the N-channel open drain output.)

I : Input O : Output I/O : Input and output

NOTES:
1. When use VCC1 > VCC2, contacts due to some points or restrictions to be checked.
2. This pin function in M16C/62PT cannot be used.
3. Ask the oscillator maker the oscillation characteristic.

Table 1.20 Pin Description (80-pin Version) (1) (1)

Signal Name	Pin Name	I/O Type	Power Supply	Description
Power supply input	VCC1, VSS	I	–	Apply 2.7 to 5.5 V to the VCC1 pin and 0 V to the VSS pin. (1, 2)
Analog power supply input	AVCC AVSS	I	VCC1	Applies the power supply for the A/D converter. Connect the AVCC pin to VCC1. Connect the AVSS pin to VSS.
Reset input	$\overline{\text{RESET}}$	I	VCC1	The microcomputer is in a reset state when applying "L" to the this pin.
CNVSS	CNVSS (BYTE)	I	VCC1	Switches processor mode. Connect this pin to VSS to when after a reset to start up in single-chip mode. Connect this pin to VCC1 to start up in microprocessor mode. As for the BYTE pin of the 80-pin versions, pull-up processing is performed within the microcomputer.
Main clock input	XIN	I	VCC1	I/O pins for the main clock generation circuit. Connect a ceramic resonator or crystal oscillator between XIN and XOUT (3). To use the external clock, input the clock from XIN and leave XOUT open.
Main clock output	XOUT	O	VCC1	
Sub clock input	XCIN	I	VCC1	I/O pins for a sub clock oscillation circuit. Connect a crystal oscillator between XCIN and XCOUT (3). To use the external clock, input the clock from XCIN and leave XCOUT open.
Sub clock output	XCOUT	O	VCC1	
Clock output	CLKOUT	O	VCC2	The clock of the same cycle as fC, f8, or f32 is outputted.
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT2}}$	I	VCC1	Input pins for the $\overline{\text{INT}}$ interrupt.
$\overline{\text{NMI}}$ interrupt input	$\overline{\text{NMI}}$	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt.
Key input interrupt input	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	VCC1	Input pins for the key input interrupt.
Timer A	TA0OUT, TA3OUT, TA4OUT	I/O	VCC1	These are Timer A0,Timer A3 and Timer A4 I/O pins. (however, output of TA0OUT for the N-channel open drain output.)
	TA0IN, TA3IN, TA4IN	I	VCC1	These are Timer A0, Timer A3 and Timer A4 input pins.
	ZP	I	VCC1	Input pin for the Z-phase.
Timer B	TB0IN, TB2IN to TB5IN	I	VCC1	These are Timer B0, Timer B2 to Timer B5 input pins.
Serial interface	$\overline{\text{CTS0}}$ to $\overline{\text{CTS1}}$	I	VCC1	These are send control input pins.
	$\overline{\text{RTS0}}$ to $\overline{\text{RTS1}}$	O	VCC1	These are receive control output pins.
	CLK0, CLK1, CLK3, CLK4	I/O	VCC1	These are transfer clock I/O pins.
	RXD0 to RXD2	I	VCC1	These are serial data input pins.
	SIN4	I	VCC1	This is serial data input pin.
	TXD0 to TXD2	O	VCC1	These are serial data output pins. (however, output of TXD2 for the N-channel open drain output.)
	SOUT3, SOUT4	O	VCC1	These are serial data output pins.
	CLKS1	O	VCC1	This is output pin for transfer clock output from multiple pins function.
I^2C mode	SDA0 to SDA2	I/O	VCC1	These are serial data I/O pins. (however, output of SDA2 for the N-channel open drain output.)
	SCL0 to SCL2	I/O	VCC1	These are transfer clock I/O pins. (however, output of SCL2 for the N-channel open drain output.)

I : Input O : Output I/O : Input and output

NOTES:
1. In this manual, hereafter, VCC refers to VCC1 unless otherwise noted.
2. In M16C/62PT, apply 4.0 to 5.5 V to the VCC1 pin.
3. Ask the oscillator maker the oscillation characteristic.

3. Memory

Figure 3.1 is a Memory Map of the M16C/62P group. The address space extends the 1M bytes from address 00000h to FFFFFh.
The internal ROM is allocated in a lower address direction beginning with address FFFFFh. For example, a 64-Kbyte internal ROM is allocated to the addresses from F0000h to FFFFFh.
As for the flash memory version, 4-Kbyte space (block A) exists in 0F000h to 0FFFFh. 4-Kbyte space is mainly for storing data. In addition to storing data, 4-Kbyte space also can store programs.
The fixed interrupt vector table is allocated to the addresses from FFFDCh to FFFFFh. Therefore, store the start address of each interrupt routine here.
The internal RAM is allocated in an upper address direction beginning with address 00400h. For example, a 10-Kbyte internal RAM is allocated to the addresses from 00400h to 02BFFh. In addition to storing data, the internal RAM also stores the stack used when calling subroutines and when interrupts are generated.
The SRF is allocated to the addresses from 00000h to 003FFh. Peripheral function control registers are located here. Of the SFR, any area which has no functions allocated is reserved for future use and cannot be used by users.
The special page vector table is allocated to the addresses from FFE00h to FFFDBh. This vector is used by the JMPS or JSRS instruction. For details, refer to the **M16C/60 and M16C/20 Series Software Manual**.
In memory expansion and microprocessor modes, some areas are reserved for future use and cannot be used by users. Use M16C/62P (80-pin version) and M16C/62PT in single-chip mode. The memory expansion and microprocessor modes cannot be used
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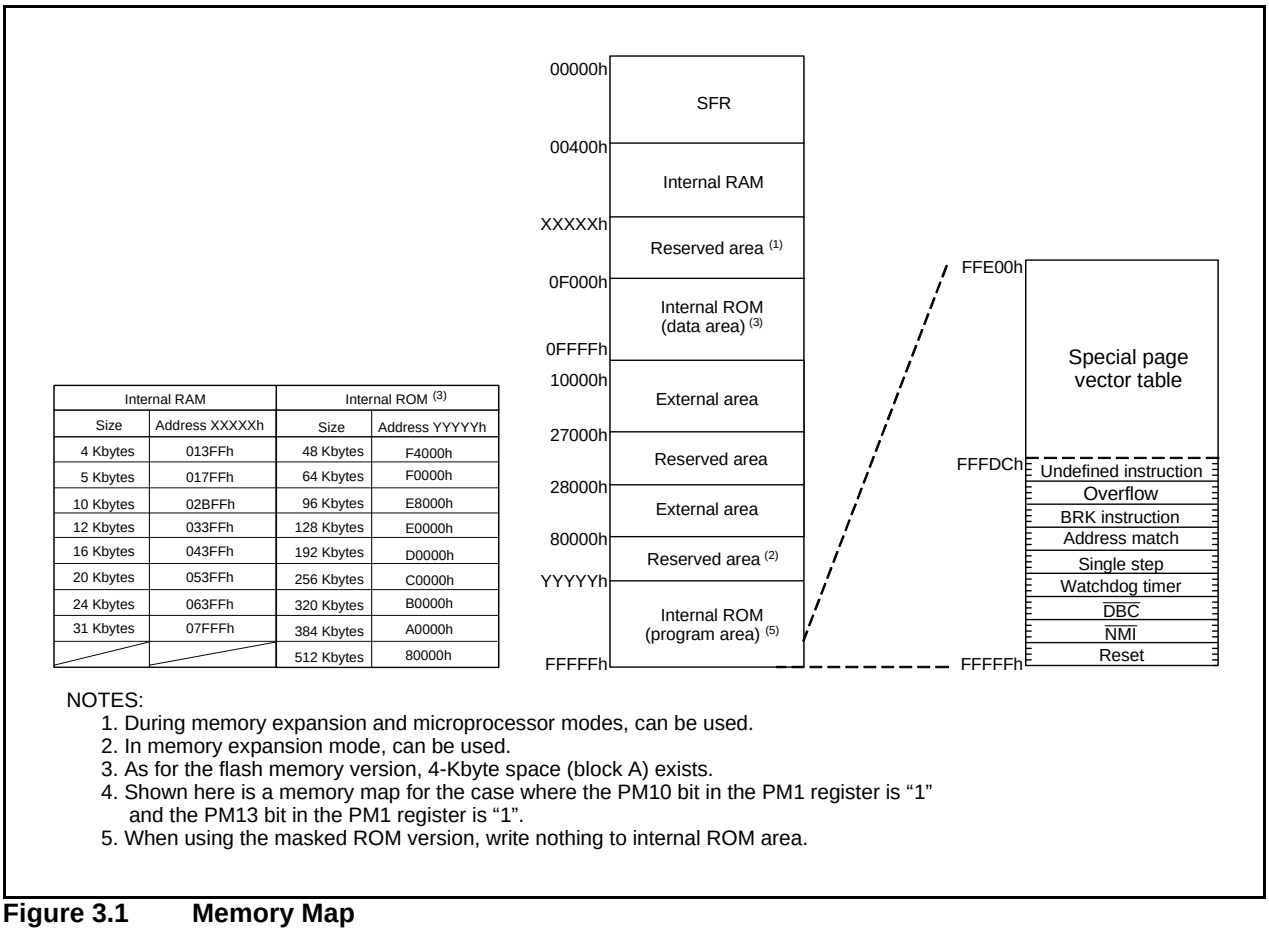


Internal RAM		Internal ROM (3)	
Size	Address XXXXXh	Size	Address YYYYYh
4 Kbytes	013FFh	48 Kbytes	F4000h
5 Kbytes	017FFh	64 Kbytes	F0000h
10 Kbytes	02BFFh	96 Kbytes	E8000h
12 Kbytes	033FFh	128 Kbytes	E0000h
16 Kbytes	043FFh	192 Kbytes	D0000h
20 Kbytes	053FFh	256 Kbytes	C0000h
24 Kbytes	063FFh	320 Kbytes	B0000h
31 Kbytes	07FFFh	384 Kbytes	A0000h
		512 Kbytes	80000h

NOTES:
1. During memory expansion and microprocessor modes, can be used.
2. In memory expansion mode, can be used.
3. As for the flash memory version, 4-Kbyte space (block A) exists.
4. Shown here is a memory map for the case where the PM10 bit in the PM1 register is “1” and the PM13 bit in the PM1 register is “1”.
5. When using the masked ROM version, write nothing to internal ROM area.

Figure 3.1 Memory Map

Table 4.3 SFR Information (3) (1)

Address	Register	Symbol	After Reset
0080h			
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h to 01AFh			
01B0h			
01B1h			
01B2h			
01B3h			
01B4h	Flash Identification Register (2)	FIDR	XXXXXX00b
01B5h	Flash Memory Control Register 1 (2)	FMR1	0X00XX0Xb
01B6h			
01B7h	Flash Memory Control Register 0 (2)	FMR0	00000001b
01B8h	Address Match Interrupt Register 2	RMAD2	00h
01B9h			00h
01BAh			XXh
01BBh	Address Match Interrupt Enable Register 2	AIER2	XXXXXX00b
01BCh	Address Match Interrupt Register 3	RMAD3	00h
01BDh			00h
01BEh			XXh
01C0h to 024Fh			
0250h			
0251h			
0252h			
0253h			
0254h			
0255h			
0256h			
0257h			
0258h			
0259h			
025Ah			
025Bh			
025Ch			
025Dh			
025Eh	Peripheral Clock Select Register	PCLKR	00000011b
025Fh			
0260h to 032Fh			
0330h			
0331h			
0332h			
0333h			
0334h			
0335h			
0336h			
0337h			
0338h			
0339h			
033Ah			
033Bh			
033Ch			
033Dh			
033Eh			
033Fh			

NOTES:
1. The blank areas are reserved and cannot be accessed by users.
2. This register is included in the flash memory version.

X : Nothing is mapped to this bit

Table 4.5 SFR Information (5) (1)

Address	Register	Symbol	After Reset
0380h	Count Start Flag	TABSR	00h
0381h	Clock Prescaler Reset Fag	CPSRF	0XXXXXXXb
0382h	One-Shot Start Flag	ONSF	00h
0383h	Trigger Select Register	TRGSR	00h
0384h	Up-Down Flag	UDF	00h (2)
0385h			
0386h	Timer A0 Register	TA0	XXh
0387h			XXh
0388h	Timer A1 Register	TA1	XXh
0389h			XXh
038Ah	Timer A2 Register	TA2	XXh
038Bh			XXh
038Ch	Timer A3 Register	TA3	XXh
038Dh			XXh
038Eh	Timer A4 Register	TA4	XXh
038Fh			XXh
0390h	Timer B0 Register	TB0	XXh
0391h			XXh
0392h	Timer B1 Register	TB1	XXh
0393h			XXh
0394h	Timer B2 Register	TB2	XXh
0395h			XXh
0396h	Timer A0 Mode Register	TA0MR	00h
0397h	Timer A1 Mode Register	TA1MR	00h
0398h	Timer A2 Mode Register	TA2MR	00h
0399h	Timer A3 Mode Register	TA3MR	00h
039Ah	Timer A4 Mode Register	TA4MR	00h
039Bh	Timer B0 Mode Register	TB0MR	00XX0000b
039Ch	Timer B1 Mode Register	TB1MR	00XX0000b
039Dh	Timer B2 Mode Register	TB2MR	00XX0000b
039Eh	Timer B2 Special Mode Register	TB2SC	XXXXXX00b
039Fh			
03A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
03A1h	UART0 Bit Rate Generator	U0BRG	XXh
03A2h	UART0 Transmit Buffer Register	U0TB	XXh
03A3h			XXh
03A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
03A5h	UART0 Transmit/Receive Control Register 1	U0C1	00XX0010b
03A6h	UART0 Receive Buffer Register	U0RB	XXh
03A7h			XXh
03A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
03A9h	UART1 Bit Rate Generator	U1BRG	XXh
03AAh	UART1 Transmit Buffer Register	U1TB	XXh
03ABh			XXh
03ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
03ADh	UART1 Transmit/Receive Control Register 1	U1C1	00XX0010b
03AEh	UART1 Receive Buffer Register	U1RB	XXh
03AFh			XXh
03B0h	UART Transmit/Receive Control Register 2	UCON	X0000000b
03B1h			
03B2h			
03B3h			
03B4h			
03B5h			
03B6h			
03B7h			
03B8h	DMA0 Request Factor Select Register	DM0SL	00h
03B9h			
03BAh	DMA1 Request Factor Select Register	DM1SL	00h
03BBh			
03BCh	CRC Data Register	CRCD	XXh
03BDh			XXh
03BEh	CRC Input Register	CRCIN	XXh
03BFh			

NOTES:
1. The blank areas are reserved and cannot be accessed by users.
2. Bit 5 in the Up-down flag is “0” by reset. However, The values in these bits when read are indeterminate.

X : Nothing is mapped to this bit

Table 5.9 Low Voltage Detection Circuit Electrical Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det4}	Low Voltage Detection Voltage (1)	V_{CC1}=0.8V to 5.5V	3.3	3.8	4.4	V
V_{det3}	Reset Level Detection Voltage (1, 2)		2.2	2.8	3.6	V
V_{det4}-V_{det3}	Electric potential difference of Low Voltage Detection and Reset Level Detection		0.3			V
V_{det3s}	Low Voltage Reset Retention Voltage				0.8	V
V_{det3r}	Low Voltage Reset Release Voltage (3)		2.2	2.9	4.0	V

NOTES:
1. $V_{det4} > V_{det3}$.
2. Where reset level detection voltage is less than 2.7 V, if the supply power voltage is greater than the reset level detection voltage, the microcomputer operates with f(BCLK) ≤ 10MHz.
3. $V_{det3r} > V_{det3}$ is not guaranteed.
4. The voltage detection circuit is designed to use when VCC1 is set to 5V.

Table 5.10 Power Supply Circuit Timing Characteristics

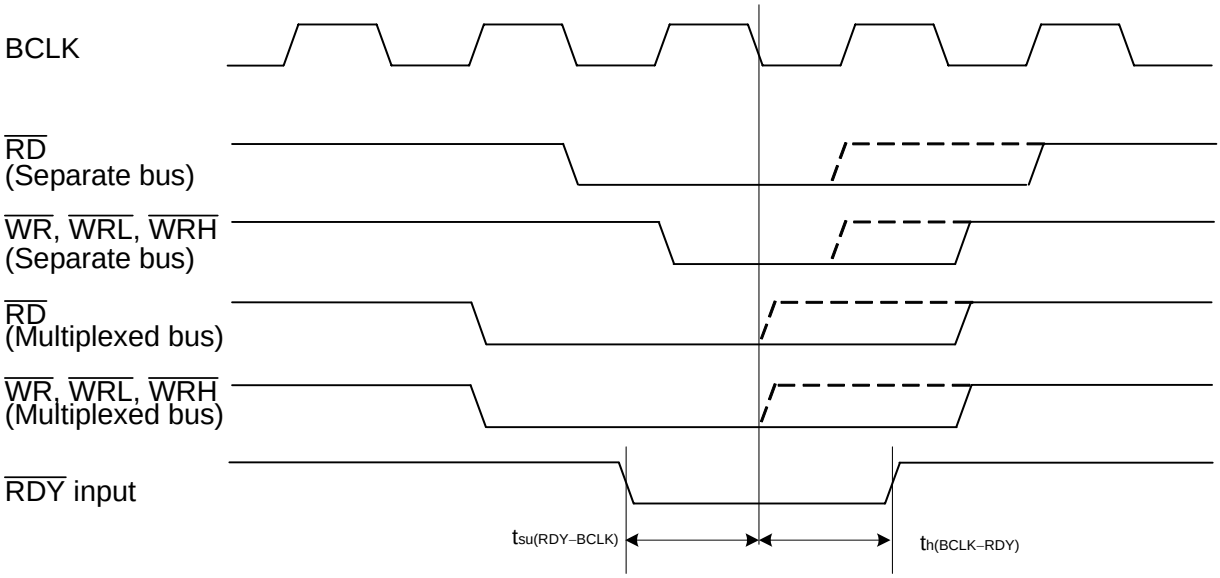
Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC1}=2.7V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				150	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	µs
$t_{d(S-R)}$	Brown-out Detection Reset (Hardware Reset 2) Release Wait Time	V_{CC1}=V_{det3r} to 5.5V		6 (1)	20	ms
$t_{d(E-A)}$	Low Voltage Detection Circuit Operation Start Time	V_{CC1}=2.7V to 5.5V			20	µs

NOTES:
1. When V_{CC1} = 5V.

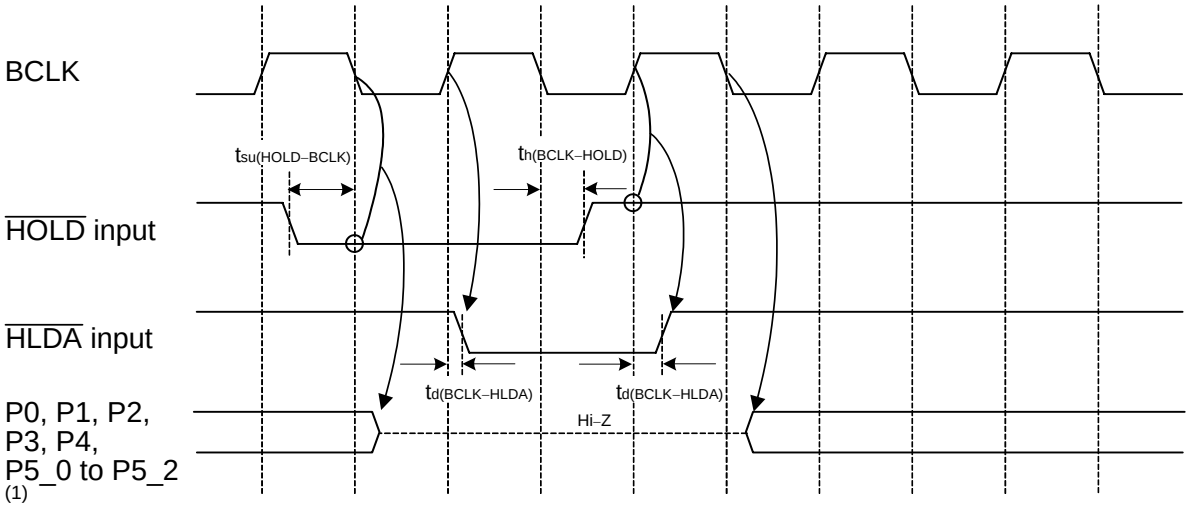
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode

(Effective for setting with wait**)**



(Common to setting with wait and setting without wait**)**



NOTES:

1. These pins are set to high-impedance regardless of the input level of the BYTE pin, PM06 bit in PM0 register and PM11 bit in PM1 register.

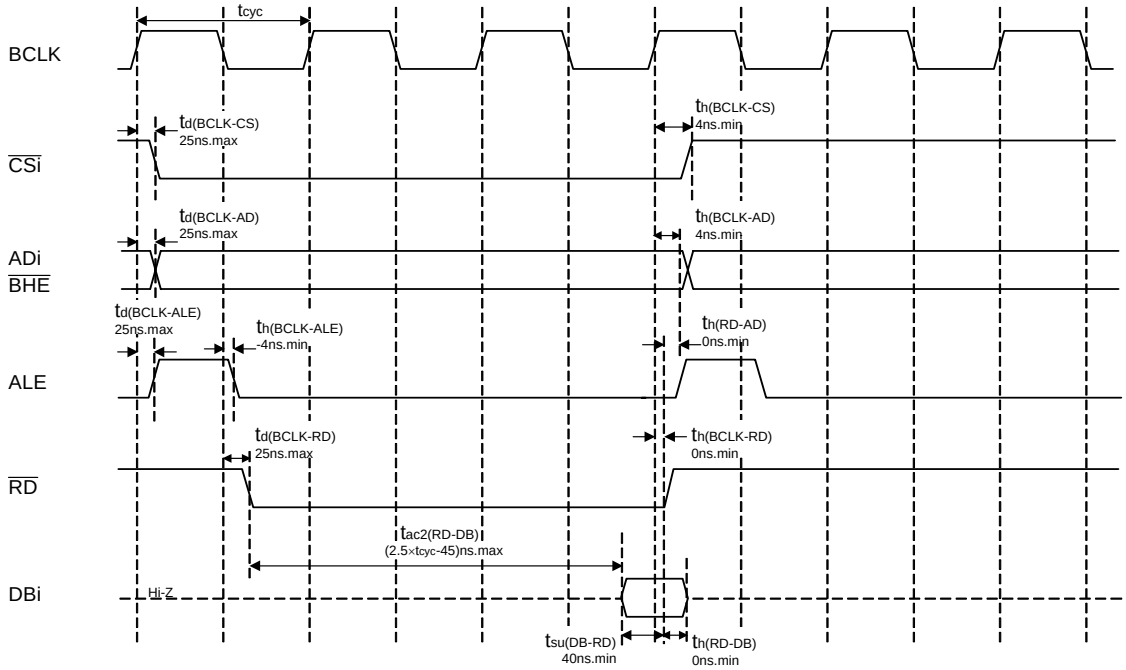
· Measuring conditions :
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : Determined with $V_{IL}=1.0V$, $V_{IH}=4.0V$
· Output timing voltage : Determined with $V_{OL}=2.5V$, $V_{OH}=2.5V$

Figure 5.5 Timing Diagram (3)

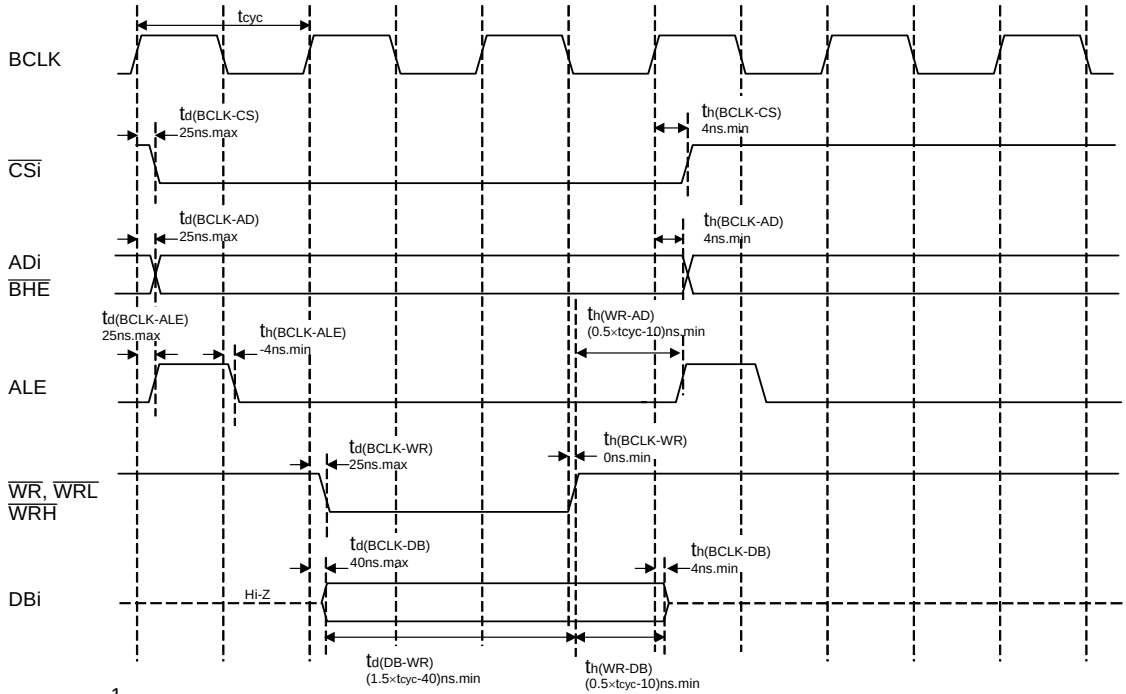
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode
(for 2-wait setting and external area access**)**

Read timing



Write timing



$$T_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.8 Timing Diagram (6)

Table 5.31 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=2.7V to 3.6V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=10MHz No division		8	11	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=10MHz, No division		8	13	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=3.0V		12		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=3.0V		22		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		45		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		6.0		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		1.8		µA
				Stop mode Topr =25°C		0.7	3.0	µA
I_{det4}	Low Voltage Detection Dissipation Current (4)					0.6	4	µA
I_{det3}	Reset Area Detection Dissipation Current (4)					0.4	2	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=2.7 to 3.3V, V_{SS} = 0V at T_{opr} = –20 to 85°C / –40 to 85°C, f(BCLK)=10MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to “1” (detection circuit enabled).

   I_{det4}: VC27 bit in the VCR2 register

   I_{det3}: VC26 bit in the VCR2 register

$V_{CC1}=V_{CC2}=3V$

Timing Requirements
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.32 External Clock Input (XIN input)(1)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	(NOTE 2)		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	(NOTE 3)		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	(NOTE 3)		ns
t_r	External Clock Rise Time		(NOTE 4)	ns
t_f	External Clock Fall Time		(NOTE 4)	ns

NOTES:
1. The condition is V_{CC1}=V_{CC2}=2.7 to 3.0V.
2. Calculated according to the V_{CC1} voltage as follows:

$$\frac{10^{-6}}{20 \times V_{CC2} - 44} \text{ [ns]}$$

3. Calculated according to the V_{CC1} voltage as follows:

$$\frac{10^{-6}}{20 \times V_{CC1} - 44} \times 0.4 \text{ [ns]}$$

4. Calculated according to the V_{CC1} voltage as follows:

$$-10 \times V_{CC1} + 45 \text{ [ns]}$$

Table 5.33 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{ac1(RD-DB)}$	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
$t_{ac2(RD-DB)}$	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
$t_{ac3(RD-DB)}$	Data Input Access Time (when accessing multiplex bus area)		(NOTE 3)	ns
$t_{su(DB-RD)}$	Data Input Setup Time	50		ns
$t_{su(RDY-BCLK)}$	$\overline{RDY}$ Input Setup Time	40		ns
$t_{su(HOLD-BCLK)}$	$\overline{HOLD}$ Input Setup Time	50		ns
$t_{h(RD-DB)}$	Data Input Hold Time	0		ns
$t_{h(BCLK-RDY)}$	$\overline{RDY}$ Input Hold Time	0		ns
$t_{h(BCLK-HOLD)}$	$\overline{HOLD}$ Input Hold Time	0		ns

NOTES:
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 60 \text{[ns]}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 60 \text{[ns]}$$ n is ”2” for 1-wait setting, “3” for 2-wait setting and “4” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 60 \text{[ns]}$$ n is “2” for 2-wait setting, “3” for 3-wait setting.

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.48 Memory Expansion and Microprocessor Modes (for 2- to 3-wait setting, external area access and multiplex bus selection)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.12**		50	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		(NOTE 1)		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			50	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-CS)}$	Chip Select Output Hold Time (in relation to RD)		(NOTE 1)		ns
$t_{h(WR-CS)}$	Chip Select Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			40	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			40	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			50	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 2)		ns
$t_{h(WR-DB)}$	Data Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time (in relation to BCLK)			25	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time (in relation to BCLK)		–4		ns
$t_{d(AD-ALE)}$	ALE Signal Output Delay Time (in relation to Address)		(NOTE 3)		ns
$t_{h(AD-ALE)}$	ALE Signal Output Hold Time (in relation to Address)		(NOTE 4)		ns
$t_{d(AD-RD)}$	RD Signal Output Delay From the End of Address		0		ns
$t_{d(AD-WR)}$	WR Signal Output Delay From the End of Address		0		ns
$t_{dz(RD-AD)}$	Address Output Floating Start Time			8	ns

NOTES:
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 50[ns]$$ n is “2” for 2-wait setting, “3” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 40[ns]$$

4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 15[ns]$$

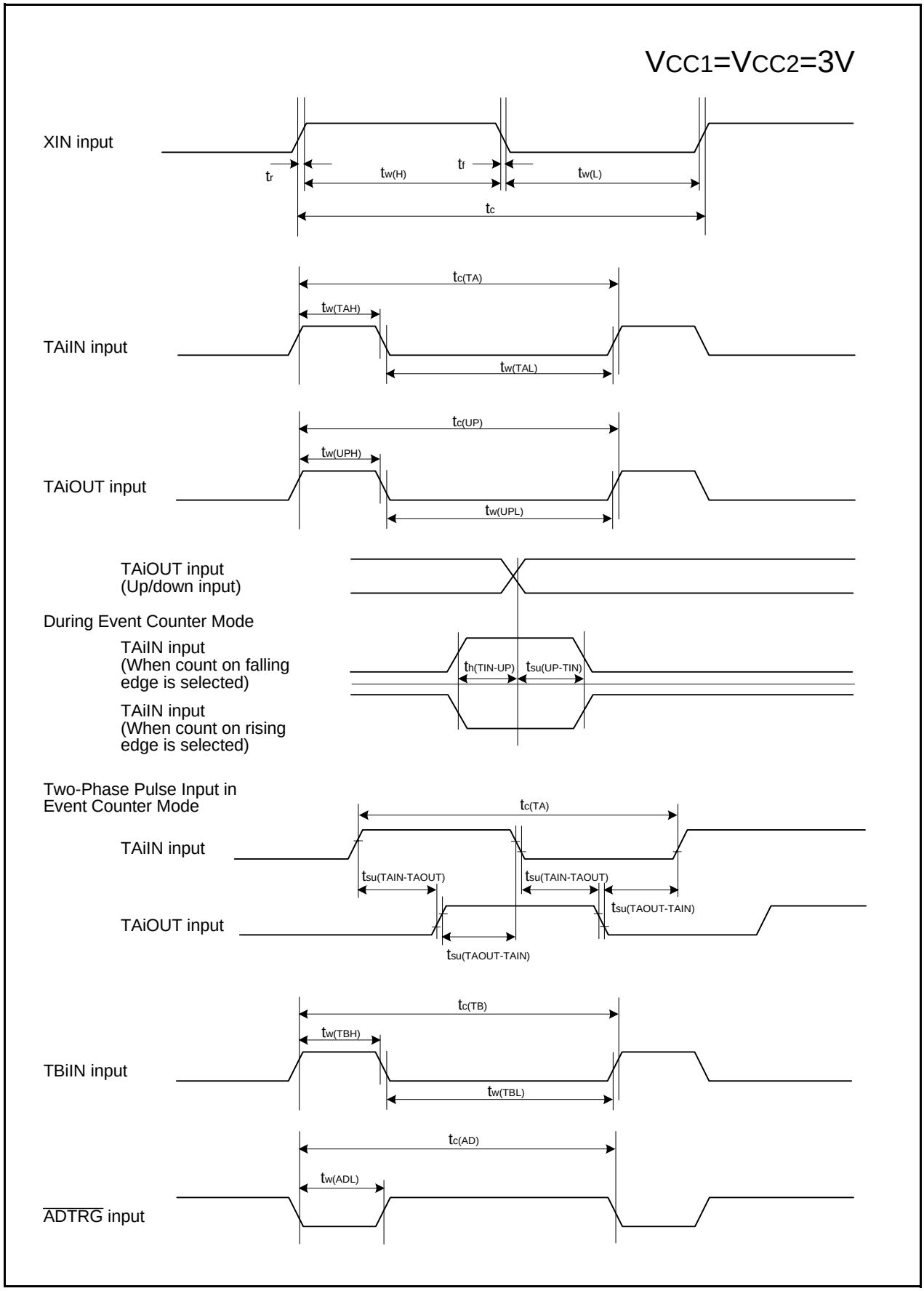


Figure 5.13 Timing Diagram (1)

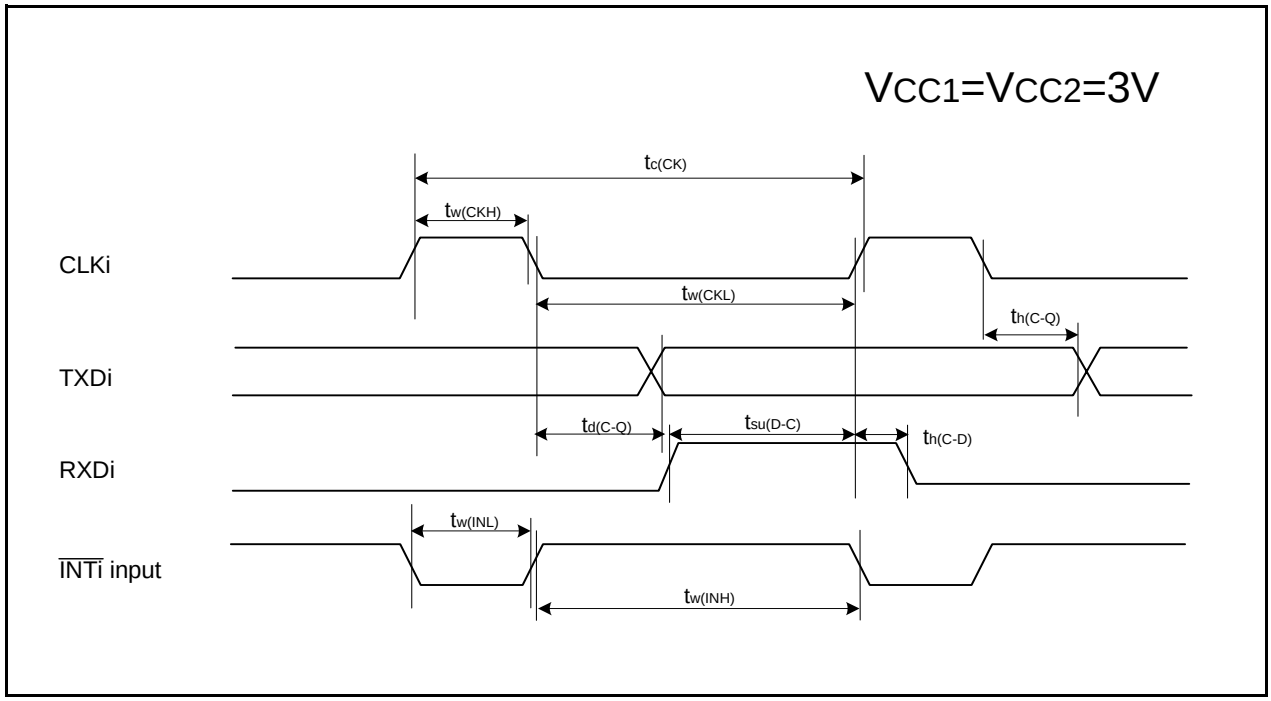
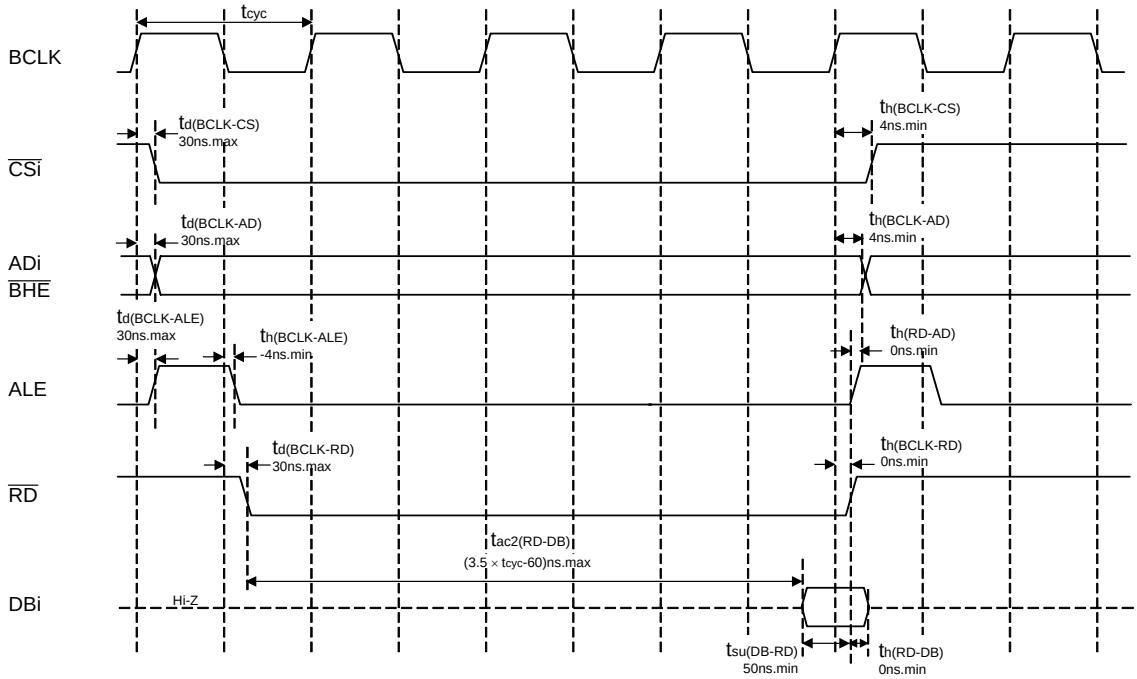


Figure 5.14 Timing Diagram (2)

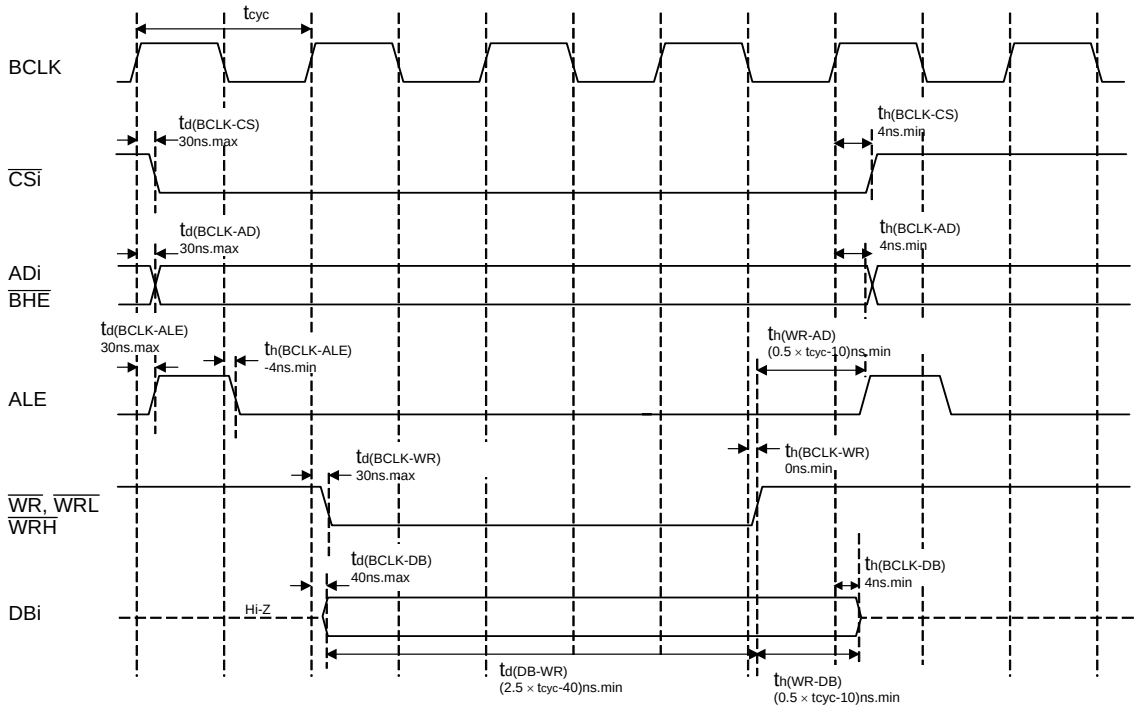
$V_{CC1} = V_{CC2} = 3V$

Memory Expansion Mode, Microprocessor Mode
(for 3-wait setting and external area access**)**

Read timing



Write timing



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
· V_{CC1}=V_{CC2}=3V
· Input timing voltage : V_{IL}=0.6V, V_{IH}=2.4V
· Output timing voltage : V_{OL}=1.5V, V_{OH}=1.5V

Figure 5.19 Timing Diagram (7)

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC}1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V

$V_{CC1}=V_{CC2}=5V$

Table 5.57 Electrical Characteristics (1) (1)

Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
V_{OH}	HIGH Output Voltage (2)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OH}=–5mA	V_{CC1}–2.0		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OH}=–5mA	V_{CC2}–2.0		V_{CC2}	
V_{OH}	HIGH Output Voltage (2)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OH}=–200μA	V_{CC1}–0.3		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OH}=–200μA	V_{CC2}–0.3		V_{CC2}	
V_{OH}	HIGH Output Voltage XOUT	HIGHPOWER	I_{OH}=–1mA	V_{CC1}–2.0		V_{CC1}	V
		LOWPOWER	I_{OH}=–0.5mA	V_{CC1}–2.0		V_{CC1}	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
V_{OL}	LOW Output Voltage (2)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OL}=5mA			2.0	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OL}=5mA			2.0	
V_{OL}	LOW Output Voltage (2)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OL}=200μA			0.45	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OL}=200μA			0.45	
V_{OL}	LOW Output Voltage XOUT	HIGHPOWER	I_{OL}=1mA			2.0	V
		LOWPOWER	I_{OL}=0.5mA			2.0	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
V_{T+}-V_{T-}	Hysteresis	HOLD, RDY, TA0IN to TA4IN, TB0IN to TB5IN, INT0 to INT5, NMI, ADTRG, CTS0 to CTS2, CLK0 to CLK4, TA0OUT to TA4OUT, KI0 to KI3, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		1.0	V
V_{T+}-V_{T-}	Hysteresis	RESET		0.2		2.5	V
I_{IH}	HIGH Input Current (2)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	V_I=5V			5.0	μA
I_{IL}	LOW Input Current (2)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	V_I=0V			–5.0	μA
R_{PULLUP}	Pull-Up Resistance (2)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	V_I=0V	30	50	170	kΩ
R_{fXIN}	Feedback Resistance XIN				1.5		MΩ
R_{fXCIN}	Feedback Resistance XCIN				15		MΩ
V_{RAM}	RAM Retention Voltage		At stop mode	2.0			V

NOTES:
1. Referenced to $V_{CC1}=V_{CC2}$=4.0 to 5.5V, V_{SS} = 0V at T_{opr} = –40 to 85°C / –40 to 125°C, f(BCLK)=24MHz unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C.
2. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

V_{CC1}=V_{CC2}=5V

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

Table 5.60 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	100		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	40		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	40		ns

Table 5.61 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	400		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	200		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	200		ns

Table 5.62 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	200		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	100		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	100		ns

Table 5.63 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	100		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	100		ns

Table 5.64 Timer A Input (Counter Increment/Decrement Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(UP)}$	TAiOUT Input Cycle Time	2000		ns
$t_{w(UPH)}$	TAiOUT Input HIGH Pulse Width	1000		ns
$t_{w(UPL)}$	TAiOUT Input LOW Pulse Width	1000		ns
$t_{su(UP-TIN)}$	TAiOUT Input Setup Time	400		ns
$t_{h(TIN-UP)}$	TAiOUT Input Hold Time	400		ns

Table 5.65 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	800		ns
$t_{su(TAIN-TAOUT)}$	TAiOUT Input Setup Time	200		ns
$t_{su(TAOUT-TAIN)}$	TAiIN Input Setup Time	200		ns

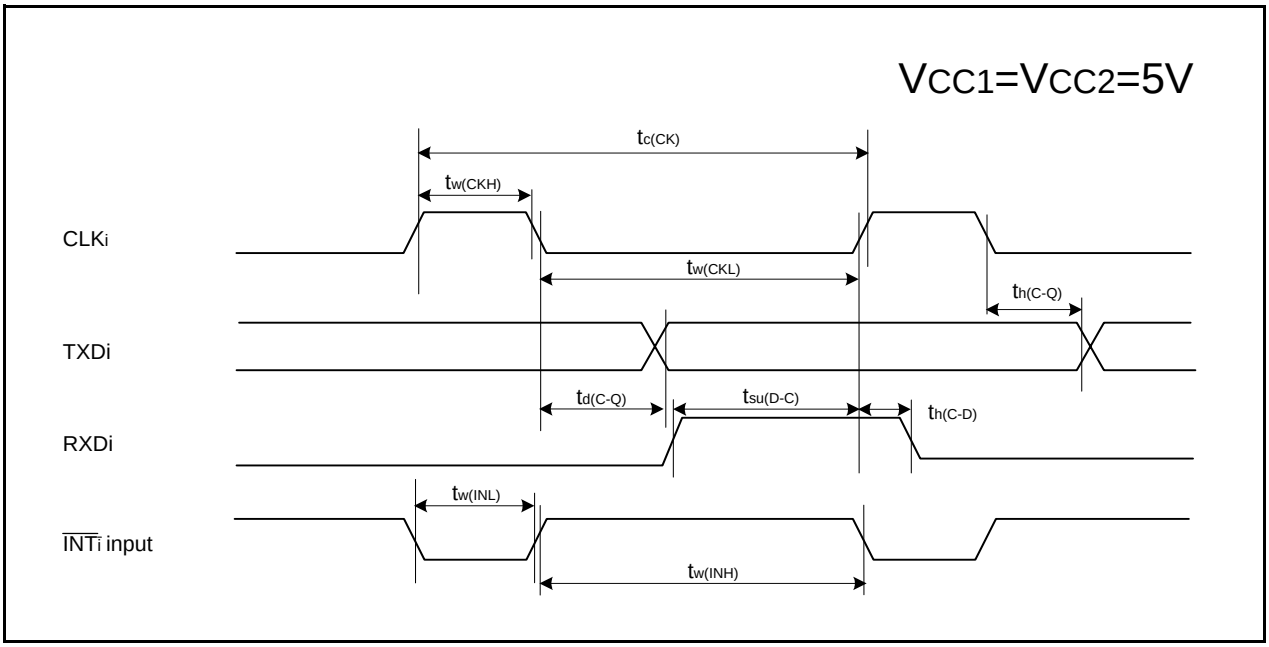
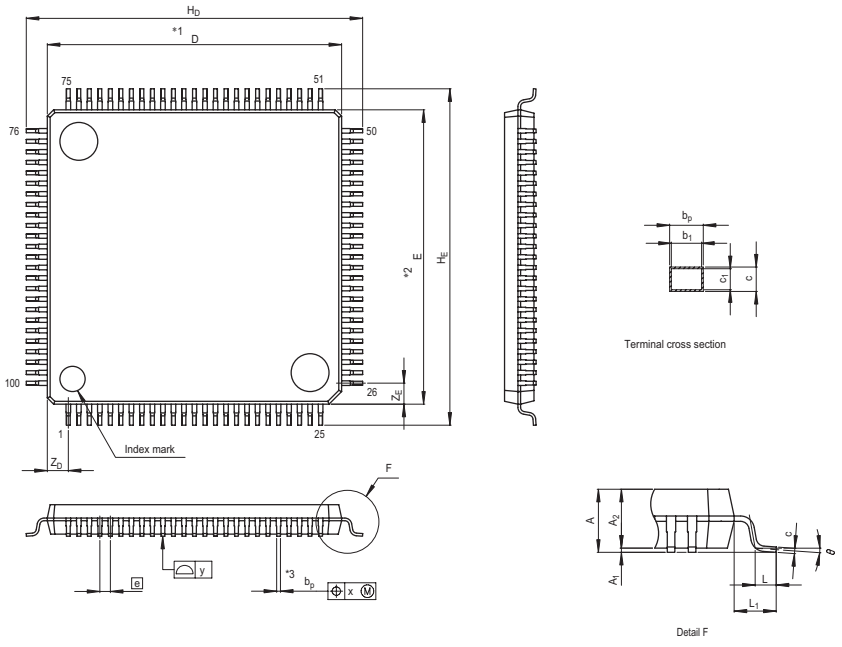


Figure 5.25 Timing Diagram (2)

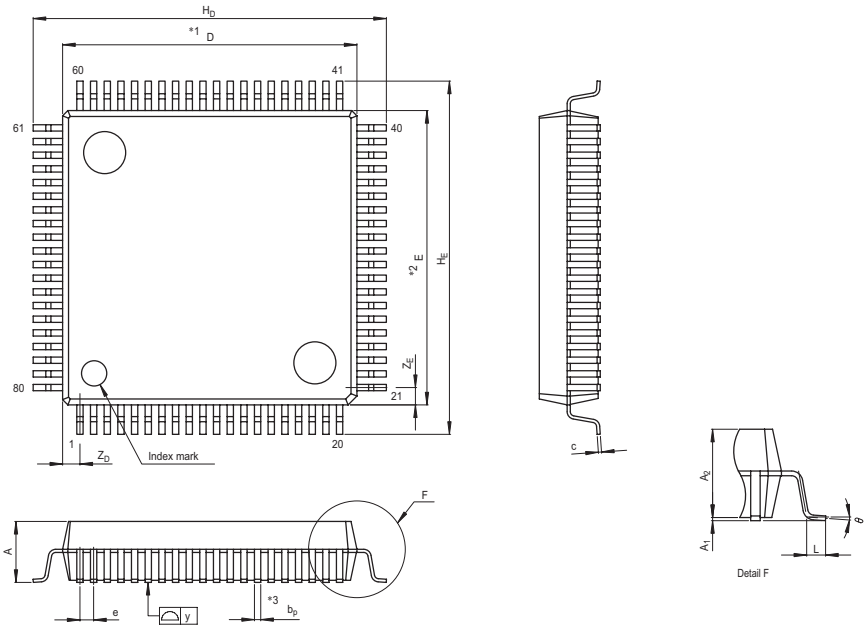
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP100-14x14-0.50	PLQP0100KB-A	100P6Q-A / FP-100U / FP-100UV	0.6g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	15.8	16.0	16.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.0	—
Z_E	—	1.0	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-QFP80-14x14-0.65	PRQP0080JA-A	80P6S-A	1.1g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.8	14.0	14.2
E	13.8	14.0	14.2
A_2	—	2.8	—
H_D	16.5	16.8	17.1
H_E	16.5	16.8	17.1
A	—	—	3.05
A_1	0	0.1	0.2
b_p	0.25	0.3	0.4
c	0.13	0.15	0.2
θ	0°	—	10°
e	0.5	0.65	0.8
y	—	—	0.10
Z_D	—	0.825	—
Z_E	—	0.825	—
L	0.4	0.6	0.8